



DMG3404L

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	25mΩ @ V _{GS} = 10V	5.8A
	35mΩ @ V _{GS} = 4.5V	4.8A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- **Power Management Functions**
- **DC-DC Converters**
- Portable Power Adaptors

N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

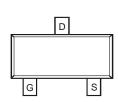
Mechanical Data

- Case: SOT23 •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminals Connections: See Diagram Below
- Weight: 0.009138 grams (Approximate)



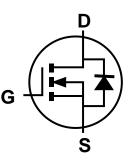
SOT23

Top View



Top View

Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3404L-7	SOT23	3000/Tape & Reel
DMG3404L-13	SOT23	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

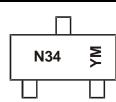
Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N34 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date	Code	Kev
Duio	oouc	1.00

Date Code Key												
Year	2012	2	2013	2014		2015	2016		2017	2018		2019
Code	Z		А	В		С	D		E	F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			VDSS	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	ID	4.2 3.5	A
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		Ι _D	5.8 4.9	А	
Pulsed Drain Current (Pulse Width ≤10µS, Duty 0	IDM	30	А		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	164	°C/W
Power Dissipation (Note 6)	PD	1.33	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	96	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	۵°

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

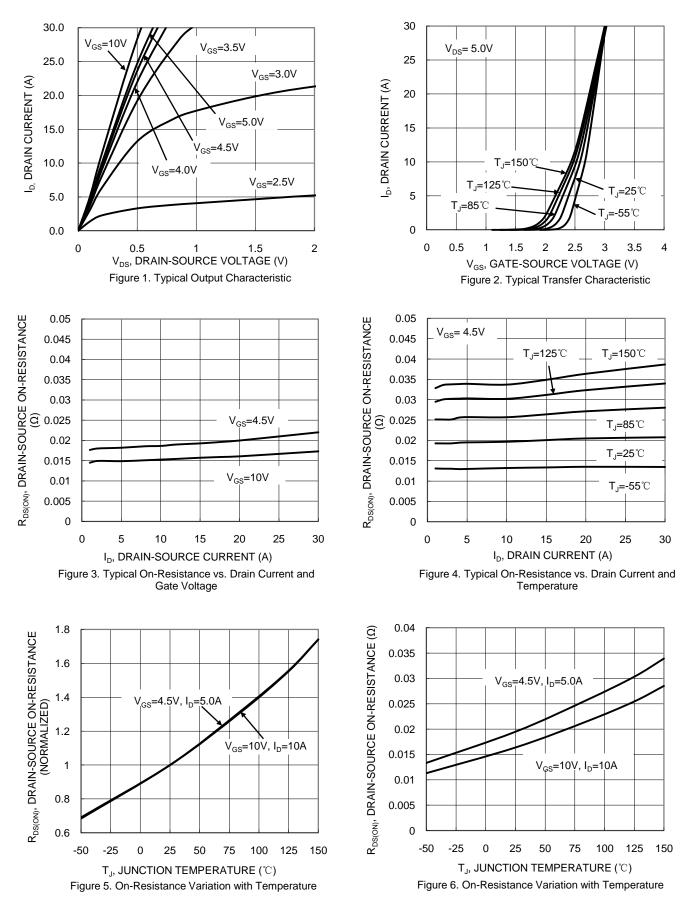
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	• •					•
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS			1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						·
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	21	25		$V_{GS} = 10V, I_D = 5.8A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	24	35	mΩ	$V_{GS} = 4.5V, I_D = 4.8A$
Diode Forward Voltage	V _{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						·
Input Capacitance	Ciss		641	—	pF	
Output Capacitance	C _{oss}	_	66	_	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	51		pF	1 = 1.0MHZ
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qq	_	13.2		nC	
Gate-Source Charge	Q _{gs}		1.7		nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 5.8A
Gate-Drain Charge	Q _{qd}	_	2.2		nC	
Turn-On Delay Time	t _{D(ON)}	_	3.3		ns	
Turn-On Rise Time	t _R		4.4		ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}		22		ns	$R_L = 1.25\Omega, R_g = 3\Omega$
Turn-Off Fall Time	tF		5.2		ns	

Notes:

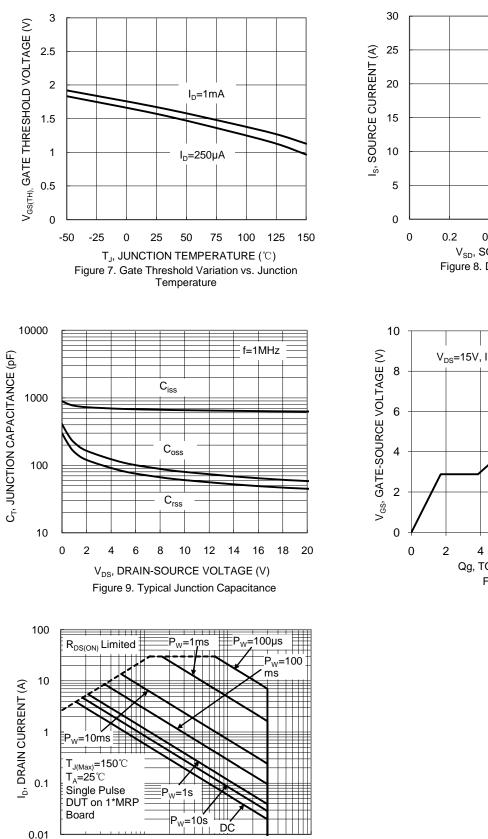
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



DMG3404L

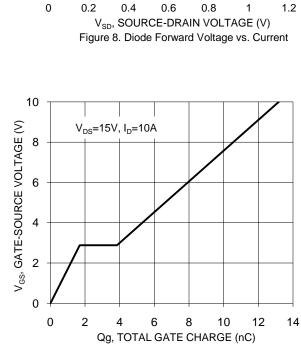






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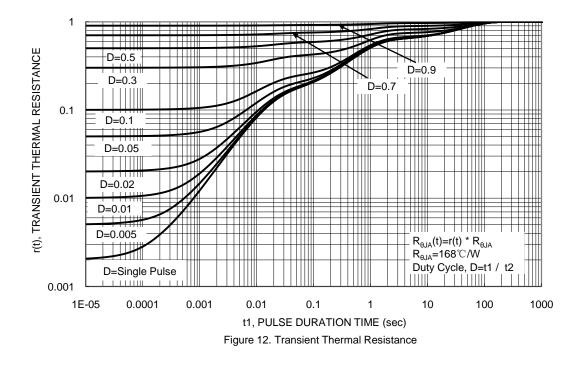
 V_{GS} =0V, T_A =25 $^{\circ}$ C

Figure 10. Gate Charge

0.1

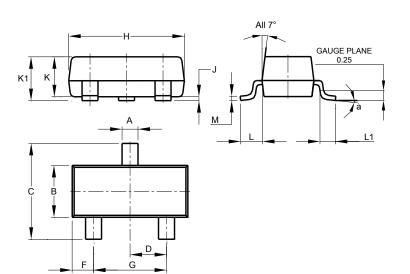
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Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



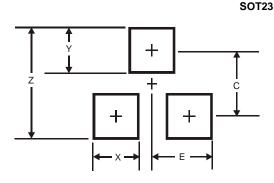
SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	8°						
All	Dimens	ions in	mm				

SOT23



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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